

5 ABSTRACT

Polycrystalline SiC plate having a preferential crystalline orientation,

said plate being characterized in that on each of its faces:

- 10 (i) its texture coefficient C_{422} is less than 40%, and
(ii) its texture coefficient $C_{220} + C_{200} + C_{400}$ is greater than 50%, and preferably greater than 80%.

This plate can be manufactured by a CVD process. The raw blank
15 thus obtained can be thinned by grinding and polishing. Its flatness, electrical conductivity and thermal conductivity, which are important properties for use as a substrate in microelectronics, can be improved by heat treatment.

20 Fig. 1